

N-Channel Enhancement-Mode MOSFET Transistors

Product Summary

Part Number	V(BR)DSS Min (V)	r _{DS(on)} Max (Ω)	V _{GS(th)} (V)	I _D (A)
TN0601L	60	1.8 @ V _{GS} = 10 V	0.5 to 2	0.47
VN0606L		3 @ V _{GS} = 10 V	0.8 to 2	0.33
VN0606M		3 @ V _{GS} = 10 V	0.8 to 2	0.39
VN66AFD		3 @ V _{GS} = 10 V	0.8 to 2.5	1.46

Features

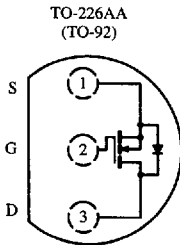
- Low On-Resistance: 1.2 Ω
- Low Threshold: <1.6 V
- Low Input Capacitance: 35 pF
- Fast Switching Speed: 9 ns
- Low Input and Output Leakage

Benefits

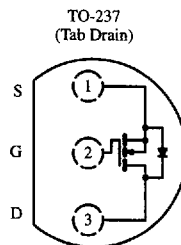
- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

Applications

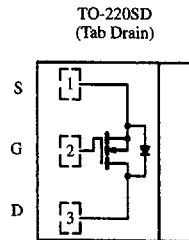
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



Top View
TN0601L
VN0606L



Top View
VN0606M



Top View
VN66AFD

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter	Symbol	TN0601L	VN0606L	VN0606M	VN66AFD ^b	Unit	
Drain-Source Voltage	V _{DS}	60	60	60	60	V	
Gate-Source Voltage	V _{GS}	±20	±30	±30	±30	V	
Continuous Drain Current (T _J = 150°C)	I _D	T _A = 25°C	0.47	0.33	0.39	1.46	A
		T _A = 100°C	0.29	0.21	0.25	0.92	
Pulsed Drain Current ^a	I _{DM}	1.5	1.6	2	3	A	
Power Dissipation	P _D	T _A = 25°C	0.8	0.8	1.0	15	W
		T _A = 100°C	0.32	0.32	0.4	6	
Maximum Junction-to-Ambient	R _{thJA}	156	156	125		°C/W	
Maximum Junction-to-Case	R _{thJC}				8.3		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150				°C	

Notes

- a. Pulse width limited by maximum junction temperature.
b. Reference case for all temperature testing.

Updates to this data sheet may be obtained via facsimile by calling Siliconix FaxBack, 1-408-970-5600. Please request FaxBack document #70201.

Specifications^a

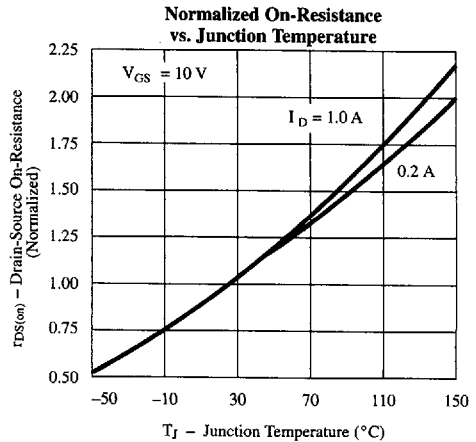
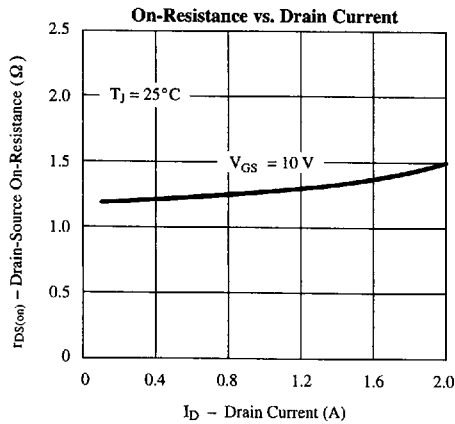
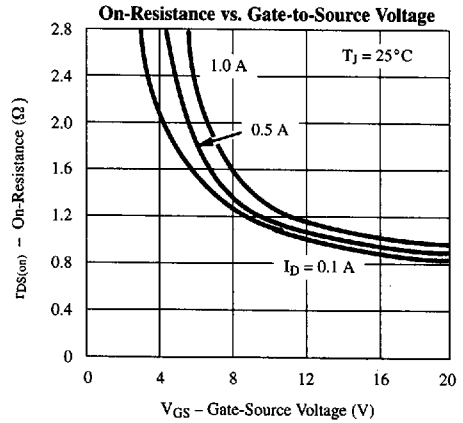
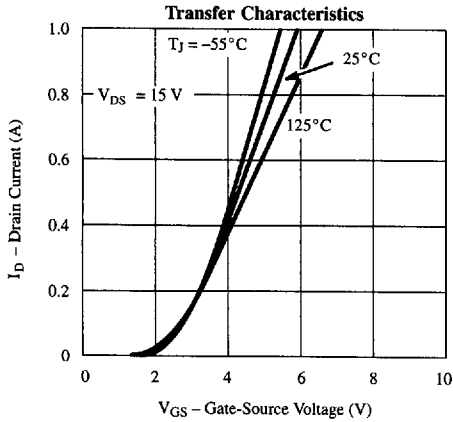
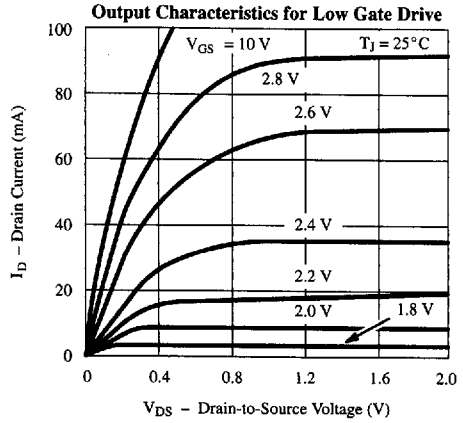
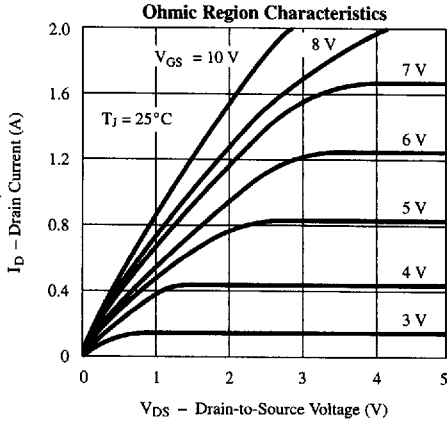
Parameter	Symbol	Test Conditions	Typ ^b	Limits						Unit	
				TN0601L		VN0606L VN0606M		VN66AFD			
				Min	Max	Min	Max	Min	Max		
Static											
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = 10\ \mu\text{A}$	70	60		60		60		V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 0.25\ \text{mA}$	1.6	0.5	2					V	
		$V_{DS} = V_{GS}, I_D = 1\ \text{mA}$	1.7			0.8	2	0.8	2.5		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}, V_{GS} = \pm 30\ \text{V}$ $T_C = 125^\circ\text{C}$					± 100		± 100	nA	
		$V_{DS} = 0\ \text{V}, V_{GS} = \pm 20\ \text{V}$			± 10						
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60\ \text{V}, V_{GS} = 0\ \text{V}$ $T_J = 125^\circ\text{C}$					10			μA	
		$V_{DS} = 48\ \text{V}, V_{GS} = 0\ \text{V}$ $T_J = 125^\circ\text{C}$			1				1		
		$T_C = 125^\circ\text{C}$			100						
		$T_C = 125^\circ\text{C}$							10		
On-State Drain Current ^c	$I_{D(on)}$	$V_{DS} = 10\ \text{V}, V_{GS} = 4.5\ \text{V}$	0.5	0.25						A	
		$V_{DS} = 10\ \text{V}, V_{GS} = 10\ \text{V}$	2.4	1		1.5		1.5			
Drain-Source On-Resistance ^c	$r_{DS(on)}$	$V_{GS} = 3.5\ \text{V}, I_D = 0.04\ \text{A}$	4		5					Ω	
		$V_{GS} = 4.5\ \text{V}, I_D = 0.25\ \text{A}$	2		3						
		$T_J = 125^\circ\text{C}$	3.8		6						
		$V_{GS} = 5\ \text{V}, I_D = 0.3\ \text{A}$	2.3					5			
		$V_{GS} = 10\ \text{V}, I_D = 0.5\ \text{A}$	1.2				3				
		$T_J = 125^\circ\text{C}$	2.3				6				
		$V_{GS} = 10\ \text{V}, I_D = 1\ \text{A}$ $T_C = 125^\circ\text{C}$	1.3		1.8				3		
Forward Transconductance ^c	g_{fs}	$V_{DS} = 10\ \text{V}, I_D = 0.5\ \text{A}$	350	200		170		170		mS	
Common Source Output Conductance ^c	g_{os}	$V_{DS} = 10\ \text{V}, I_D = 0.1\ \text{A}$	0.3							mS	
Dynamic											
Input Capacitance	C_{iss}	$V_{DS} = 25\ \text{V}, V_{GS} = 0\ \text{V},$ $f = 1\ \text{MHz}$	35		60		50		50	pF	
Output Capacitance	C_{oss}		25		50		40		40		
Reverse Transfer Capacitance	C_{rss}		6		10		10		10		
Switching^d											
Turn-On Time	t_{ON}	$V_{DD} = 25\ \text{V}, R_L = 23\ \Omega$ $I_D \approx 1\ \text{A}, V_{GEN} = 10\ \text{V}$	8		15		10		15	ns	
Turn-Off Time	t_{OFF}	$R_G = 25\ \Omega$	9		15		10		15		

Notes

- $T_A = 25^\circ\text{C}$ unless otherwise noted.
- For DESIGN AID ONLY, not subject to production testing.
- Pulse test: $PW \leq 300\ \mu\text{s}$ duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

VNDQ06

Typical Characteristics (25°C Unless Otherwise Noted)



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Low Power MOSFETs

Typical Characteristics (25°C Unless Otherwise Noted)

